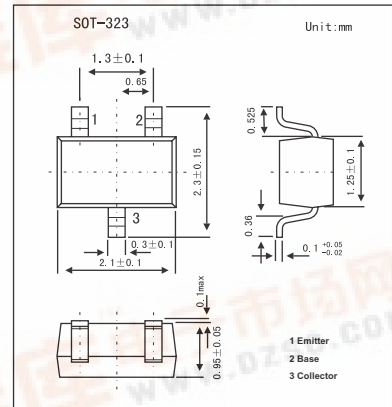


SMD Type Transistors

High Frequency Amplifier  
2SC4774

■ Features

- Very low output-on resistance (Ron).
- Low capacitance.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	12	V
Collector-emitter voltage	V <sub>CEO</sub>	6	V
Emitter-base voltage	V <sub>EB0</sub>	3	V
Collector current	I <sub>C</sub>	50	mA
Collector power dissipation	P <sub>C</sub>	0.2	W
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	BV <sub>CB0</sub>	I <sub>C</sub> =10μA	12			V
Collector-emitter voltage	BV <sub>CEO</sub>	I <sub>C</sub> =1mA	6			V
Emitter-base voltage	BV <sub>EB0</sub>	I <sub>E</sub> =10μA	3			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> =10V			0.5	μA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> =2V			0.5	μA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> /I <sub>B</sub> =10mA/1mA			0.3	V
Forward current transfer ratio	h <sub>FE</sub>	V <sub>CE</sub> /I <sub>C</sub> =5V/5mA	270		560	
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>E</sub> =-10mA, f=200MHz	300	800		MHz
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0A, f=1MHz		1	1.7	pF
Output-on resistance	R <sub>on</sub>	I <sub>B</sub> =3mA, V <sub>I</sub> =100mV <sub>rms</sub> , f=500kHz		2		Ω

■ Marking

Marking	BMS
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